Schottky barrier diode

RB706F-40 / RB706D-40

●Applications

General purpose detection
High speed switching

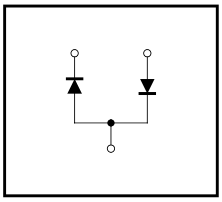
●Features

1) Small surface mounting dual element linear type.
(SMD3, UMD3)
2) Low V_F and low I_R.
3) High reliability.

●Construction

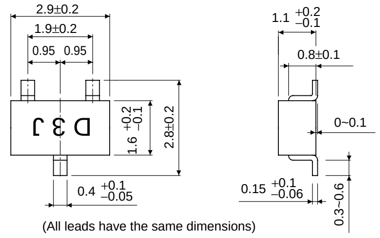
Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)

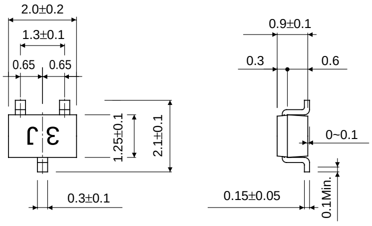
RB706D-40



(All leads have the same dimensions)

ROHM : SMD3
EIAJ : SC-59
JEDEC : SOT-346

RB706F-40



(All leads have the same dimensions)

ROHM : UMD3
EIAJ : SC-70
JEDEC : SOT-323

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	45	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current *	I_{FSM}	200	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−40~+125	°C

∗60 Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.37	V	I_F=1mA
Reverse current	I_R	–	–	1	µA	V_R=10V
Capacitance between terminals	C_T	–	2.0	–	pF	V_R=1V, f=1MHz

Note) ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C)

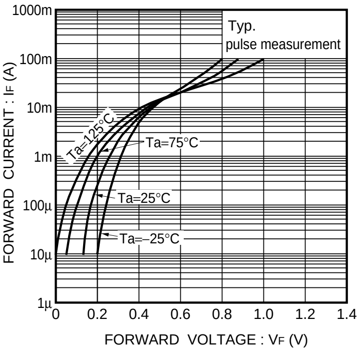


Fig. 1 Forward characteristics

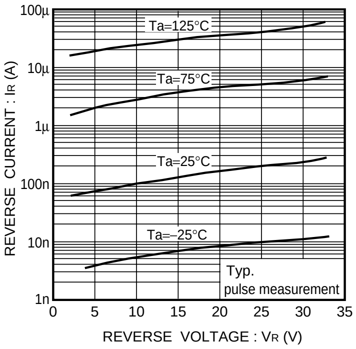


Fig. 2 Reverse characteristics

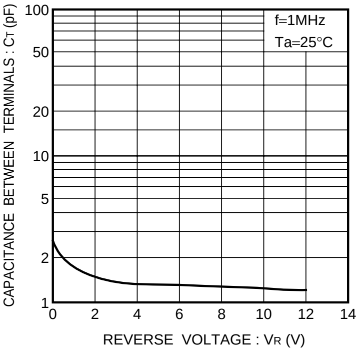


Fig. 3 Capacitance between terminals characteristics

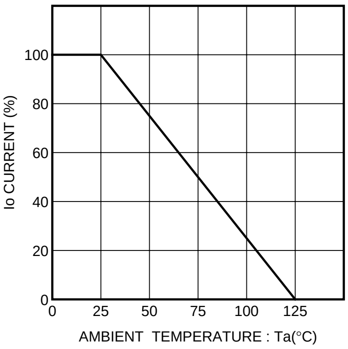


Fig 4. Derating curve
(mounting on glass epoxy PCBs)